

# Type 2N5154L Geometry 9201 Polarity NPN Qual Level: JAN - JANS

### Features:

- Silicon power transistor for use in high speed switching applications.
- Housed in a TO-5 case.
- Also available in chip form using the 9201 chip geometry.
- The Min and Max limits shown are per MIL-PRF-19500/544 which Semicoa meets in all cases.

### Data Sheet No. 2N5154L

Generic Part Number: 2N5154L

## REF: MIL-PRF-19500/544



## **Maximum Ratings**

Rating	Symbol	Rating	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	80	V
Collector-Base Voltage	V <sub>CBO</sub>	100	V
Emitter-Base Voltage	V <sub>EBO</sub>	5.5	V
Collector Current, Continuous	Ι <sub>C</sub>	2	A
Collector Current, $P_W < 8.3$ ms, $< 1\%$ duty cycle	Ι <sub>C</sub>	10	А
Reverse Pulse Energy		15	mJ
Power Disipation $T_A = 25^{\circ}C$ ambient Derate above $25^{\circ}C$	P <sub>T</sub>	1.0 5.7	Watt mW/°C
Operating Junction Temperature	TJ	-65 to +200	°C
Storage Temperature	T <sub>STG</sub>	-65 to +200	°C

## $T_{\rm C} = 25^{\circ}$ C unless otherwise specified



# **Electrical Characteristics**

T <sub>C</sub> = 25°C un	less otherwise	e specified		
OFF Characteristics	Symbol	Min	Max	Unit
Collector-Base Breakdown Voltage $I_{C} = 100 \text{ mA}, I_{B} = 0, \text{ pulsed}$	V <sub>(BR)CBO</sub>	80		V
Base-Emitter Cutoff Current				
$V_{EB} = 4 V, I_{C} = 0$	I <sub>EBO1</sub>		1.0	μA
$V_{EB} = 5.5 \text{ V}, \text{ I}_{C} = 0$	I <sub>EBO2</sub>		1.0	mA
Collector-Emitter Cutoff Current				
$V_{CE} = 60 \text{ V}, \text{ V}_{BE} = 0$	I <sub>CES1</sub>		1.0	μA
$V_{CE} = 100 \text{ V}, \text{ V}_{BE} = 0$	I <sub>CES2</sub>		1.0	mA
$V_{CE} = 40 \text{ V}, \text{ I}_{B} = 0$	I <sub>CEO</sub>		50	μA
$V_{CE} = 60 \text{ V}, \text{ V}_{BE} = -2 \text{ V}, \text{ T}_{C} = 150^{\circ}\text{C}$	I <sub>CEX</sub>		500	μA
ON Characteristics	Symbol	Min	Max	Unit
Forward Current Transfer Ratio				
$I_{C} = 50 \text{ mA}, V_{CE} = 5 \text{ V}$	h <sub>FE1</sub>	50 70		
$I_C = 2.5 \text{ A}, V_{CE} = 5 \text{ V}, \text{ pulsed}$ $I_C = 5.0 \text{ A}, V_{CE} = 5 \text{ V}, \text{ pulsed}$	h <sub>FE2</sub> b	70 40	200	
$I_{\rm C} = 3.0$ A, $V_{\rm CE} = 3$ V, pulsed $I_{\rm C} = 2.55$ A, $V_{\rm CE} = 5$ V pulsed, $T_{\rm C} = -55$ °C	h <sub>FE3</sub> h <sub>FE4</sub>	40 25		
Base-Emitter Voltage, Nonsaturted	• • • • • • • • • • • • • • • • • • • •	20		
$V_{CE} = 5 \text{ V}, I_C = 2.5 \text{ A}, \text{ pulsed}$	V <sub>BE</sub>		1.45	V dc
Base-Emitter Saturation Voltage	51			
$I_{\rm C} = 2.5 \text{ A}, I_{\rm B} = 250 \text{ mA}, \text{ pulsed}$	V <sub>BE(sat)1</sub>		1.45	V dc
$I_{\rm C}$ = 5 A, $I_{\rm B}$ = 500 mA, pulsed	V <sub>BE(sat)2</sub>		2.2	V dc
Collector-Emitter Saturation Voltage				
$I_{\rm C}$ = 2.5 A, $I_{\rm B}$ = 250 mA, pulsed	V <sub>CE(sat)1</sub>		0.75	V dc
$I_{\rm C}$ = 5 A, $I_{\rm B}$ = 500 mA, pulsed	V <sub>CE(sat)2</sub>		1.5	V dc
Small Signal Characteristics	Symbol	Min	Max	Unit
Magnitude of Common Emitter Small Signal Short Circuit Forward Current Transfer Ratio $V_{CE} = 5 \text{ V}, I_C = 500 \text{ mA}, f = 10 \text{ MHz}$	h <sub>fe</sub>	7.0		
Common Emitter, Small Signal Short Circuit Forward Current Transfer Ratio $V_{CE} = 5 \text{ V}, I_C = 100 \text{ mA}, f = 1 \text{ kHz}$	h <sub>fe</sub>	50		
Open Circuit Output Capacitance $V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	C <sub>OBO</sub>		250	pF
Switching Time	Symbol	Min	Max	Unit
Delay Time $I_{\rm C} = 5 \text{ A}, I_{\rm B1} = 500 \text{ mA}$	t <sub>ON</sub>		0.5	μs
Storage Time I <sub>B2</sub> = -500 mA	t <sub>s</sub>		1.4	μs
Fall Time V <sub>BE(off)</sub> = 3.7 V	t <sub>f</sub>		0.5	μs
Tum-Off Time $R_L = 6 \text{ ohms}$	t <sub>OFF</sub>		1.5	μs